MICROWAVE POWER GaAs FET

RF Performance Specifications ($T_a = 25$ °C)

Characteristic	Symbol	Condition	Unit	Min.	Тур.	Max.
Output Power at 1dB Compression Point	P _{1dB}	V _{DS} = 9V f = 10.7 ~ 11.7 GHz	dBm	41.0	42.0	_
Power Gain at 1dB Compression Point	G _{1dB}		dB	6.0	7.0	_
Drain Current	I _{DS1}		Α	-	4.5	5.5
3rd Order Intermodulation Distortion	IM ₃	Note 1	dBc	-42	-45	-
Drain Current	I _{DS2}		Α	-	4.5	5.5

Note 1: 2-tone Test Pout, Po = 30 dBm Single Carrier Level.

Electrical Characteristics (T_a = 25°C)

Characteristic	Symbol	Condition	Unit	Min.	Тур.	Max.
Transconductance	gm	V _{DS} = 3V I _{DS} = 4.8A	mS	-	3000	-
Pinch-off Voltage	V _{GSoff}	V _{DS} = 3V I _{DS} = 145 mA	V	-1.5	-3.0	-4.5
Saturated Drain Current	I _{DSS}	$V_{DS} = 3V$ $V_{GS} = 0V$	Α	_	10.0	11.5
Gate-Source Breakdown Voltage	V _{GSO}	I _{GS} = -145 μA	٧	-5	-	-
Thermal Resistance	R _{th (c-c)}	Channel to Case	°C/W	-	2.0	2.5

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